

[LOW TEMPERATURE POLYSILICON THIN FILM TRANSISTOR AND METHOD OF MANUFACTURING THE SAME]

Abstract

A low temperature polysilicon thin film transistor and method of manufacturing the same is provided. The low temperature polysilicon thin film transistor comprises a channel region. Among others, one feature of the method according to the present invention is the performance of a plasma treatment to adjust the threshold voltage of the low temperature polysilicon thin film transistor. Because the threshold voltage of the low temperature polysilicon thin film transistor can be adjusted through a plasma treatment, the manufacturing process is more flexible.